

ACTT8B-800CTN Enhanced and high temperature ACTT power switch 14 May 2015 Product Product data sheet

General description 1.

AC Thyristor Triac power switch in a SOT404 (D2PAK) surface mountable plastic package with self-protective clamping capabilities against low and high energy transients. This "series CTN" triac will commutate the full RMS current at the maximum rated junction temperature (T_{i(max)} = 150 °C) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

Features and benefits 2.

- Clamping structure ensuring safe high over-voltage withstand capability
- High junction operating temperature capability ($T_{i(max)} = 150 \text{ °C}$)
- High minimum IGT for guaranteed immunity to gate noise
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Less sensitive gate for high noise immunity
- Surface mountable package
- Triggering in three quadrants only
- Very high immunity to false turn-on by dV/dt and IEC 61000-4-4 fast transient
- Package meets UL94V0 flammability requirement
- Package is RoHS compliant

3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls
- Applications subject to high temperature (T_{i(max)} = 150 °C)

Quick reference data 4.

Table 1. Quid	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off- state voltage		-	-	800	V





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{TSM}	non-repetitive peak on- state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4</u> ; <u>Fig. 5</u>	-	-	80	A
Tj	junction temperature		-	-	150	°C
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 131 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	8	А
V _{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; Fig. 6	-	-	2	kV
Static char	acteristics	· · · · · · · · · · · · · · · · · · ·				
I _{GT}	gate trigger current	V_D = 12 V; I _T = 100 mA; LD+ G+; T _j = 25 °C; <u>Fig. 8</u>	5	-	35	mA
		V _D = 12 V; I _T = 100 mA; LD+ G-; T _j = 25 °C; <u>Fig. 8</u>	5	-	35	mA
		V _D = 12 V; I _T = 100 mA; LD- G-; T _j = 25 °C; <u>Fig. 8</u>	5	-	35	mA
V _{CL}	clamping voltage	I _{CL} = 0.1 mA; t _p = 1 ms; T _j = 25 °C	850	-	-	V
Dynamic c	haracteristics	· · · · · · · · · · · · · · · · · · ·				
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	4000	-	-	V/µs
		V_{DM} = 536 V; T _j = 150 °C; exponnetial waveform; gate open circuit	2000	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 150 °C; $I_{T(RMS)}$ = 8 A; dV _{com} /dt = 20 V/µs; gate open circuit; snubberless condition	12	-	-	A/ms
		SHUDDENESS CONULION				

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	СМ	common	mb	LD
2	LD	load		
3	G	gate		G' CM
mb	LD	mounting base; load	D2PAK (SOT404A)	003aaf296

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6. Ordering information

Table 3. Ordering inf	formation		
Type number	Package		
	Name	Description	Version
ACTT8B-800CTN	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404A

7. Marking

Table 4. Marking codes	
Type number	Marking code
ACTT8B-800CTN	ACTT8B-800CTN

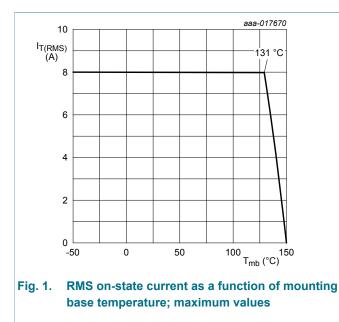
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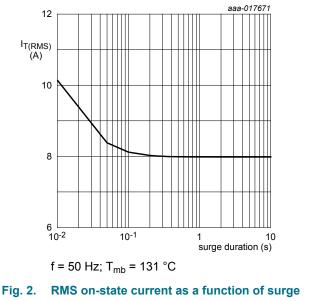
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

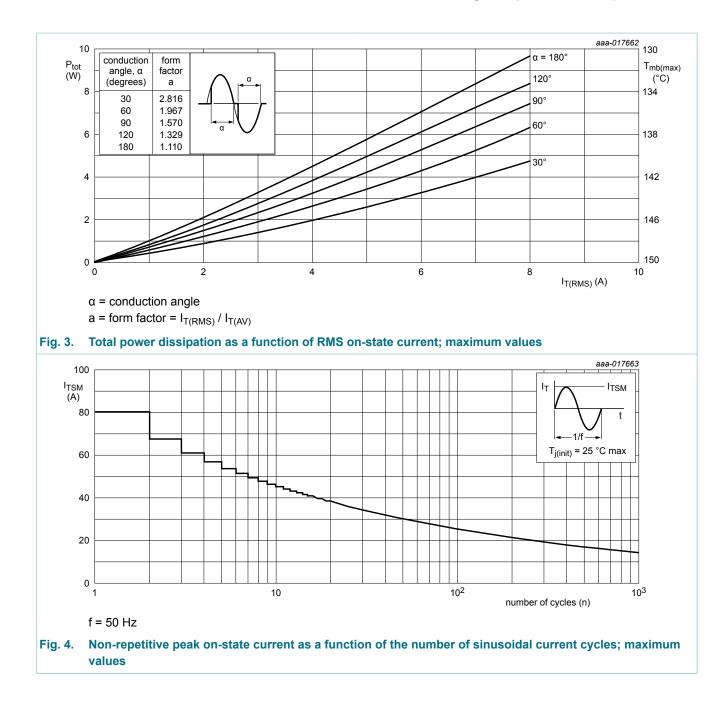
Symbol	Parameter	Conditions	M	lin l	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-		800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 131 °C; <u>Fig. 1;</u> Fig. 2; <u>Fig. 3</u>	-		8	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; <u>Fig. 4; Fig. 5</u>	-		80	A
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-		88	A
l ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-		32	A ² s
dl _T /dt	rate of rise of on-state current	I _G = 70 mA	-		100	A/µs
I _{GM}	peak gate current	t = 20 μs	-		2	А
P _{GM}	peak gate power		-		5	W
P _{G(AV)}	average gate power	over any 20 ms period	-		0.5	W
T _{stg}	storage temperature		-4	40	150	°C
Tj	junction temperature		-		150	°C
V _{PP}	peak pulse voltage	T _j = 25 °C; non-repetitive, off-state; Fig. 6	-		2	kV





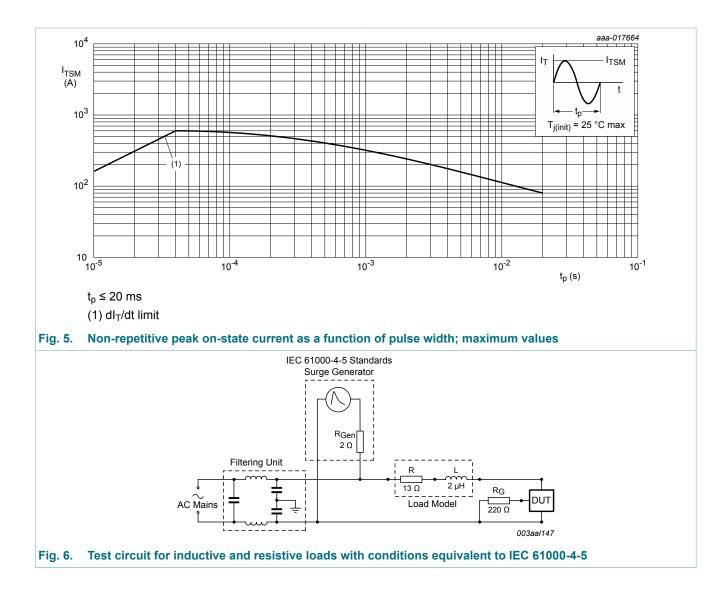
duration; maximum values

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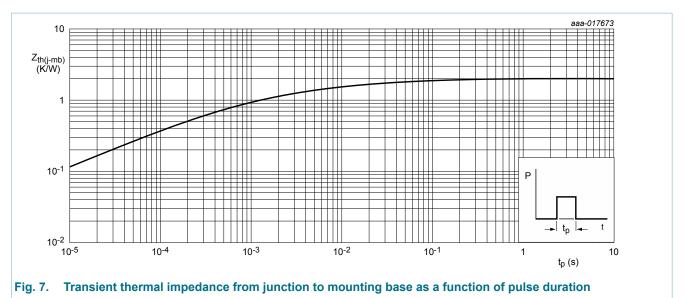
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9. Thermal characteristics

Table 6. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance	full cycle; <u>Fig. 7</u>	-	-	2	K/W
	from junction to mounting base	half cycle	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air; printed circuit board (FR4) mounted	-	55	-	K/W



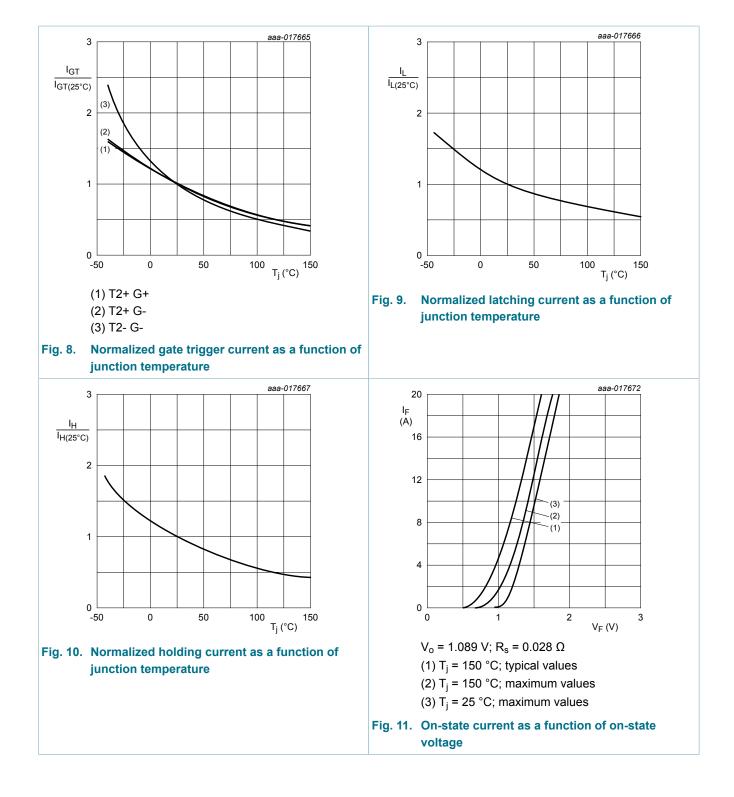
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	1				
I _{GT}	gate trigger current	V_D = 12 V; I _T = 100 mA; LD+ G+; T _j = 25 °C; Fig. 8	5	-	35	mA
		V_D = 12 V; I _T = 100 mA; LD+ G-; T _j = 25 °C; <u>Fig. 8</u>	5	-	35	mA
		V_D = 12 V; I _T = 100 mA; LD- G-; T _j = 25 °C; Fig. 8	5	-	35	mA
IL	latching current	V_D = 12 V; I _G = 100 mA; LD+ G+; T _j = 25 °C; <u>Fig. 9</u>	-	-	50	mA
		V_D = 12 V; I _G = 100 mA; LD+ G-; T _j = 25 °C; <u>Fig. 9</u>	-	-	60	mA
		V_D = 12 V; I _G = 100 mA; LD- G-; T _j = 25 °C; <u>Fig. 9</u>	-	-	50	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 10</u>	-	-	40	mA
V _T	on-state voltage	I _T = 10 A; T _j = 25 °C; <u>Fig. 11</u>	-	-	1.5	V
V _{GT}	gate trigger voltage	V _D = 12 V; I _T = 100 mA; T _j = 25 °C; Fig. 12	-	0.8	1	V
		V _D = 400 V; I _T = 100 mA; T _j = 150 °C; Fig. 12	0.2	0.45	-	V
I _D	off-state current	V _D = 800 V; T _j = 25 °C	-	-	10	μA
		V _D = 800 V; T _j = 150 °C	-	-	2	mA
V _{CL}	clamping voltage	I _{CL} = 0.1 mA; t _p = 1 ms; T _j = 25 °C	850	-	-	V
Dynamic cł	naracteristics	1 I				
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T _j = 125 °C; (V _{DM} = 67% of V _{DRM}); exponential waveform; gate open circuit	4000	-	-	V/µs
		V_{DM} = 536 V; T _j = 150 °C; exponnetial waveform; gate open circuit	2000	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$\label{eq:VD} \begin{split} V_D &= 400 \text{ V}; \text{T}_{j} = 150 ^\circ\text{C}; \text{I}_{\text{(RMS)}} = 8 \text{ A}; \\ \text{d} \text{V}_{\text{com}}/\text{d} \text{t} = 20 \text{ V}/\mu\text{s}; \text{ gate open circuit}; \\ \text{snubberless condition} \end{split}$	12	-	-	A/ms
		$V_{D} = 400 \text{ V}; \text{T}_{\text{j}} = 150 ^{\circ}\text{C}; \text{I}_{\text{T}(\text{RMS})} = 8 \text{ A};$ $dV_{\text{com}}/dt = 10 \text{ V}/\mu\text{s}; \text{ gate open circuit}$	15	-	-	A/ms
		V_D = 400 V; T _j = 150 °C; I _{T(RMS)} = 8 A; dV _{com} /dt = 1 V/µs; gate open circuit	20	-	-	A/ms

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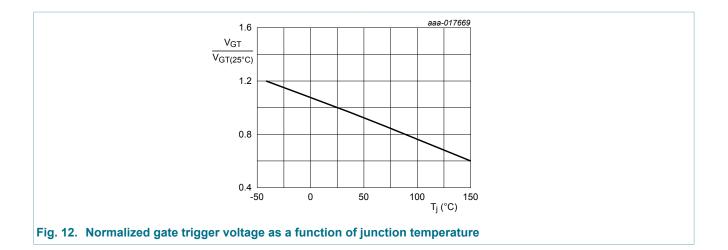


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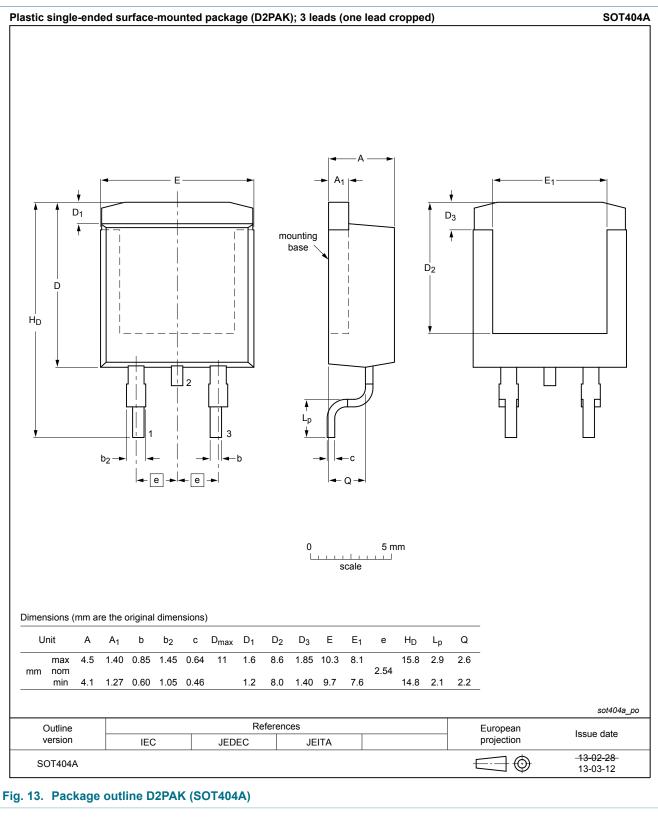
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11. Package outline



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12. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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